

Ordering number: ENN6072A

N-Channel Silicon MOSFET



FTD2011

Load Switching Applications

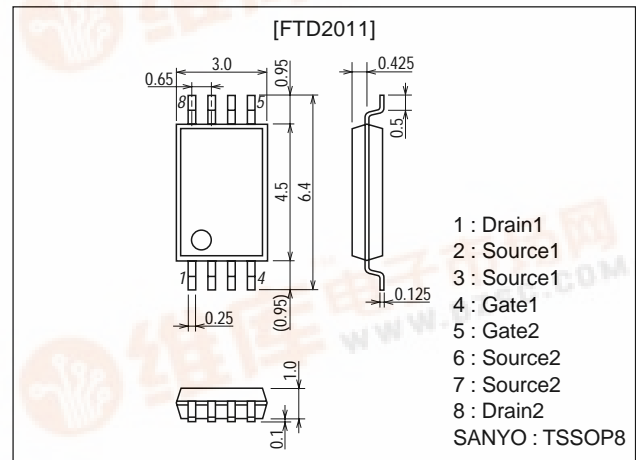
Features

- Low ON resistance.
- 2.5V drive.
- Mounting height 1.1mm.
- Composite type, facilitating high-density mounting.

Package Dimensions

unit:mm

2155A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		20	V
Gate-to-Source Voltage	V_{GS}		± 10	V
Drain Current (DC)	I_D		5	A
Drain Current (pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	20	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1000mm ² ×0.8mm) 1 unit	0.8	W
Total Dissipation	P_T	Mounted on a ceramic board (1000mm ² ×0.8mm)	1.3	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA$, $V_{GS}=0$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V$, $V_{GS}=0$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V$, $V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V$, $I_D=1mA$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V$, $I_D=5A$	8	12		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=4A$, $V_{GS}=4V$		22	28	m Ω
	$R_{DS(on)2}$	$I_D=2A$, $V_{GS}=2.5V$		30	40	m Ω
Input Capacitance	C_{iss}	$V_{DS}=10V$, $f=1MHz$		900		pF
Output Capacitance	C_{oss}	$V_{DS}=10V$, $f=1MHz$		260		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V$, $f=1MHz$		200		pF

Marking : D2011

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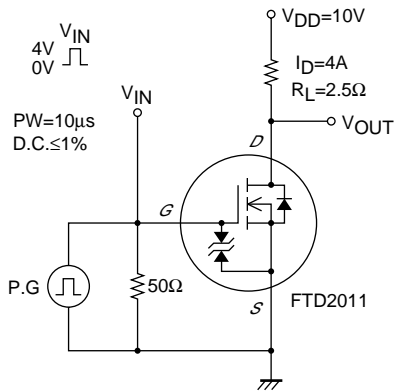


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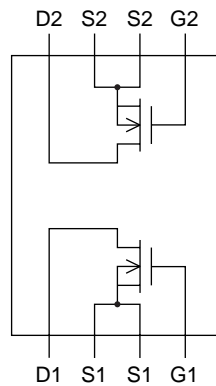
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See Specified Test Circuit		15		ns
Rise Time	t_r	See Specified Test Circuit		150		ns
Turn-OFF Delay Time	$t_{d(off)}$	See Specified Test Circuit		100		ns
Fall Time	t_f	See Specified Test Circuit		150		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=10V, I_D=4A$		32		nC
Gate-to-Source Charge	Qgs			1.5		nC
Gate-to-Drain "Miller" Charge	Qgd			6		nC
Diode Forward Voltage	VSD	$I_S=5A, V_{GS}=0$	0.82	1.2		V

Switching Time Test Circuit

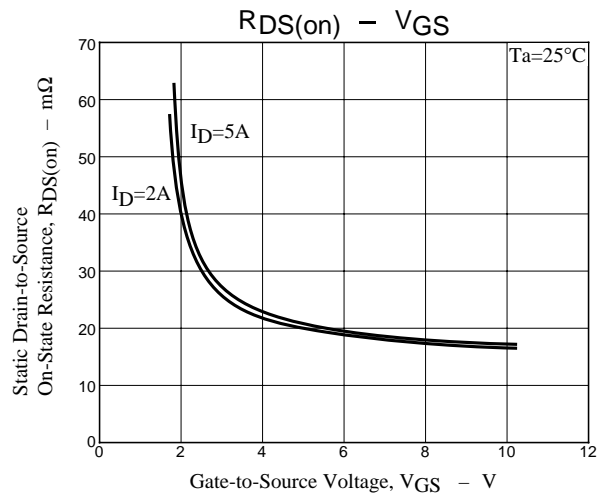
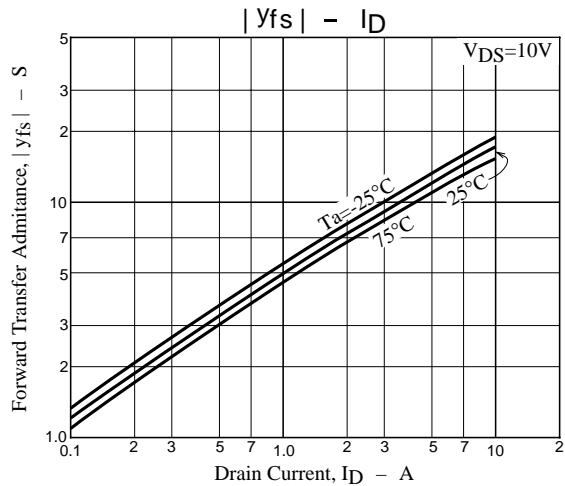
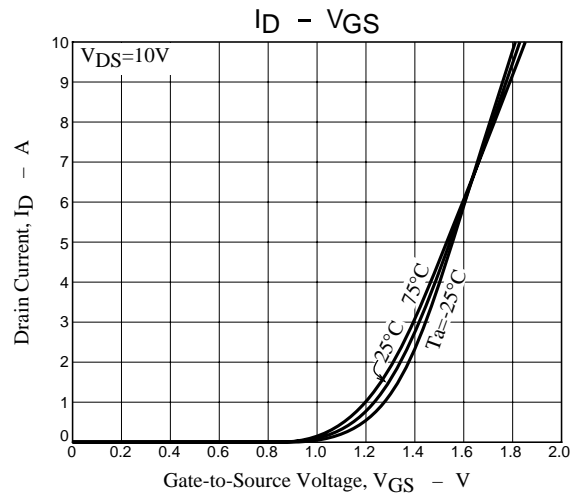
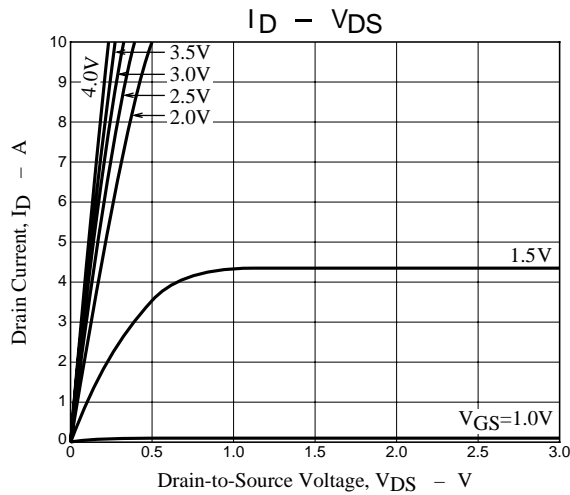


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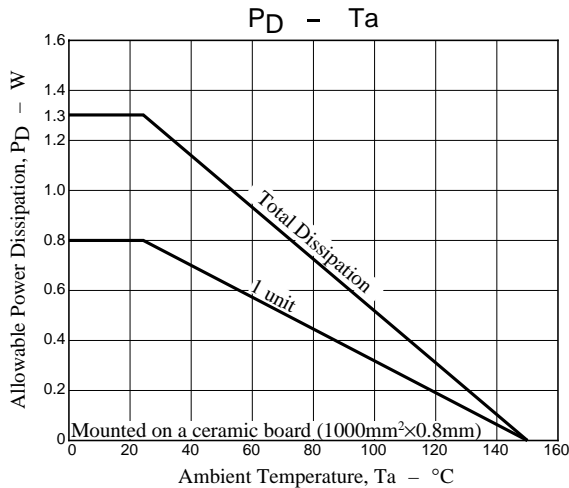
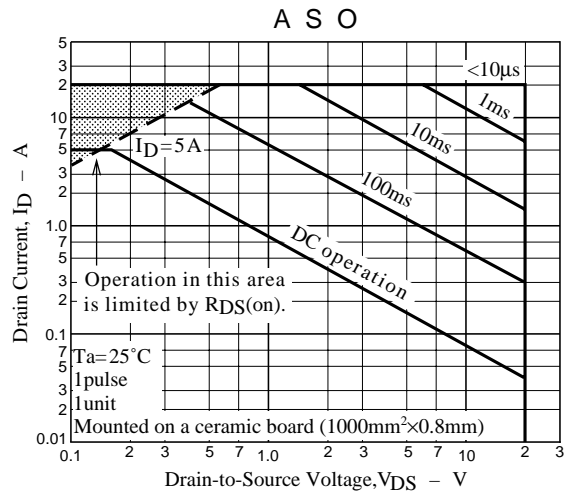
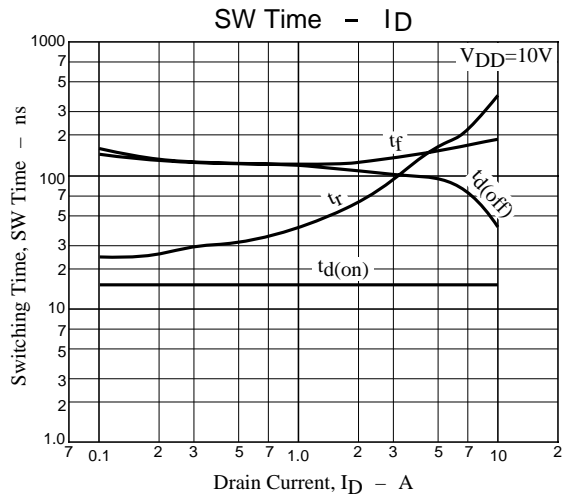
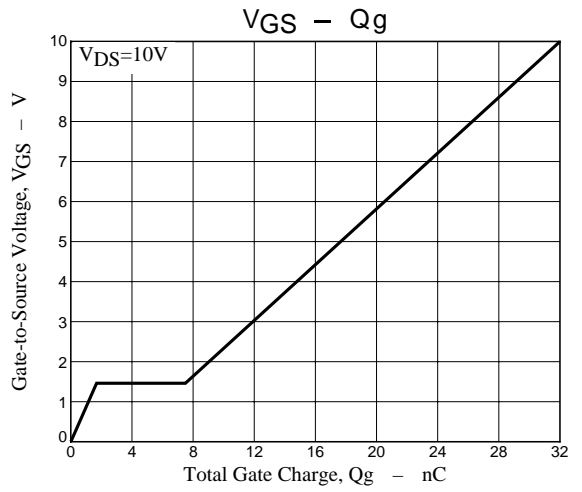
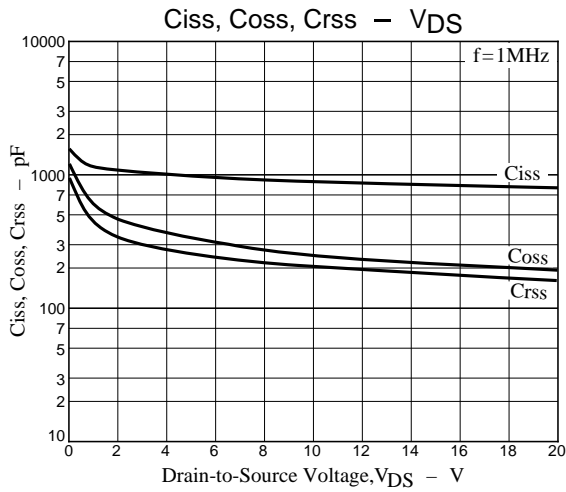
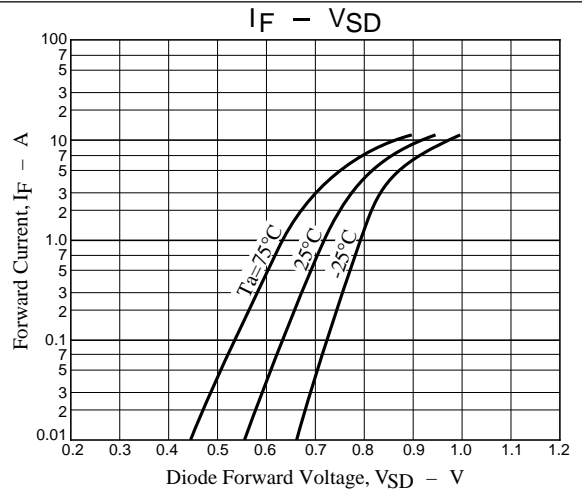
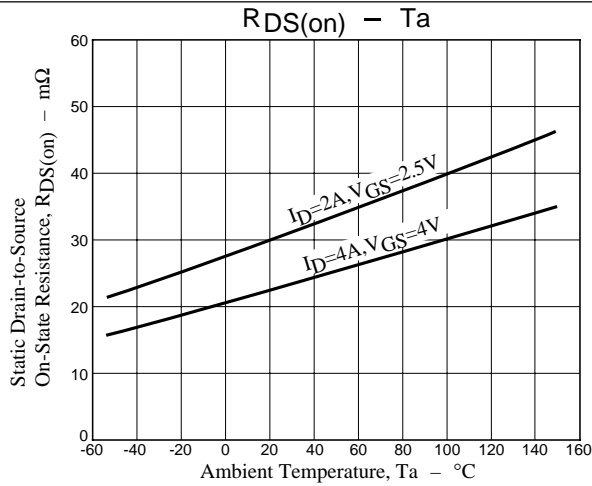
Electrical Connection



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